

SOD-523 Schottky Barrier Diode 肖特基势垒二极管
Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	BAT46X	
Pin 管脚	 	
Mark 打标	S9	

Absolute Maximum Ratings 最大额定值

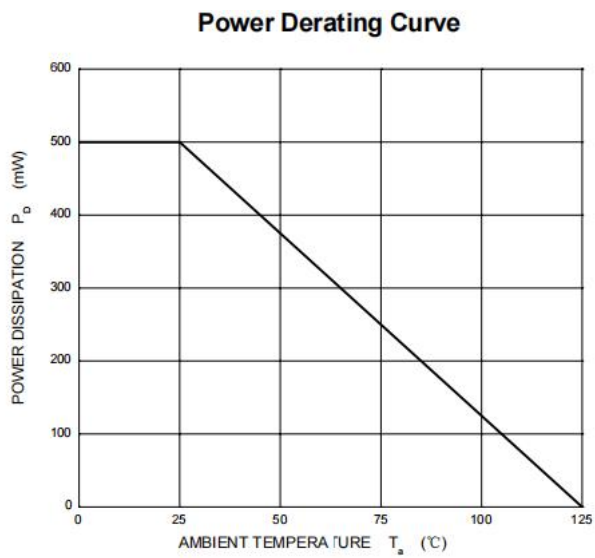
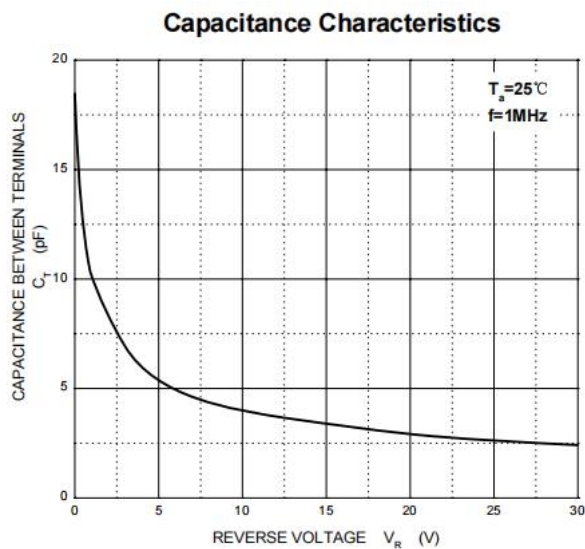
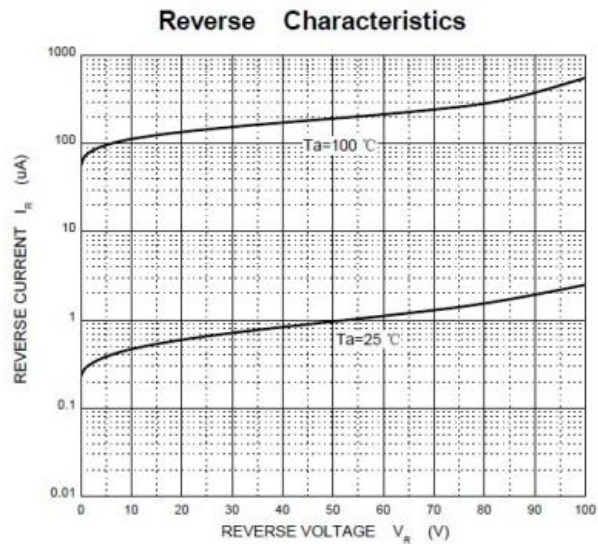
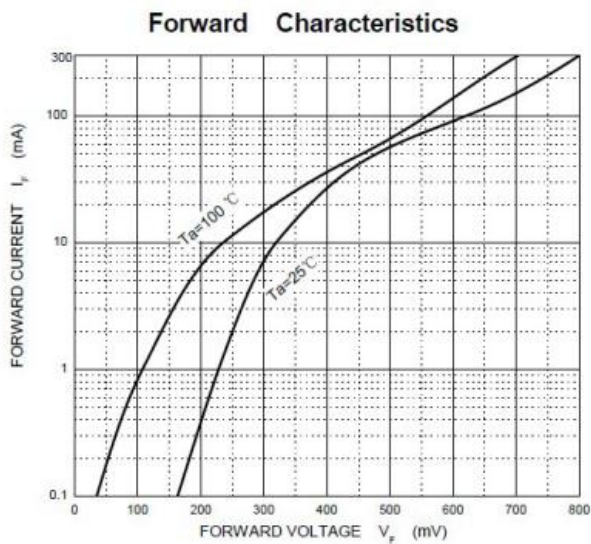
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	100	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
DC Reverse Voltage 直流反向电压	V_R		
Forward Work Current 正向工作电流	$I_F(I_O)$	150	mA
Repetitive Peak Forward Current 正向峰值电流	I_{FRM}	350	mA
Non-repetitive Peak Forward Surge Current 正向峰值浪涌电流	I_{FSM}	750	mA
Power dissipation 耗散功率	$P_D(T_a=25^{\circ}C)$	200	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	500	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	125, -55 to +150 $^{\circ}C$	

Electrical Characteristics 电特性

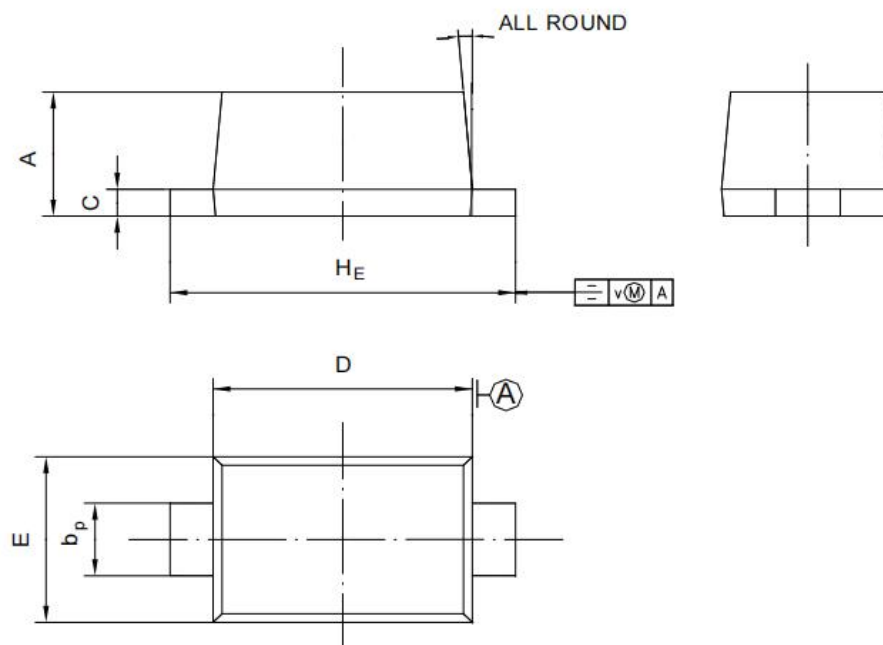
($T_A=25^{\circ}C$ unless otherwise noted 如无特殊说明, 温度为 $25^{\circ}C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=100\mu A$)	$V_{(BR)}$	100	—	—	V
Reverse Leakage Current($V_R=50V$) 反向漏电流($V_R=75V$)	I_R	—	—	1 2	μA
Forward Voltage($I_F=0.1mA$) 正向电压($I_F=10mA$) ($I_F=250mA$)	V_F	—	—	0.3 0.45 1	V
Diode Capacitance($V_R=0V, f=1MHz$) 二极管电容($V_R=1V, f=1MHz$)	C_D	—	20 12	—	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.68 0.58	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°